

M. Bruzzi - Proposal of activity in New Material

	SiC	GaN	Diamond	Epitaxial Si
Max thickness achievable [μm]				
Max size wafer achievable				
e-h per μm for mips				
Cce % before irr. with mips				
#e collected before irr				
#e collected after $1\text{e}15\text{n}/\text{cm}^2$				
#e collected after $1\text{e}16\text{ n}/\text{cm}^2$				
#e collected after $1\text{e}15\text{ 24GeV pcm}^{-2}$				
#e collected after $1\text{e}16\text{ 24GeV pcm}^{-2}$				
Annealing data ...				

p-CVD and s-CVD Diamond (Data from RD42 Status report Jan. 2006)

Polycrystalline: CEE% 0.2 at $1.8 \times 10^{16} \text{cm}^{-2}$ corresponds to 2160e if a $300 \mu\text{m}$ ccd is reached before irradiation.

Single crystal: CCE % 0.32 at $5 \times 10^{15} \text{cm}^{-2}$ corresponds to 5760e if a $500 \mu\text{m}$ ccd is reached before irradiation.

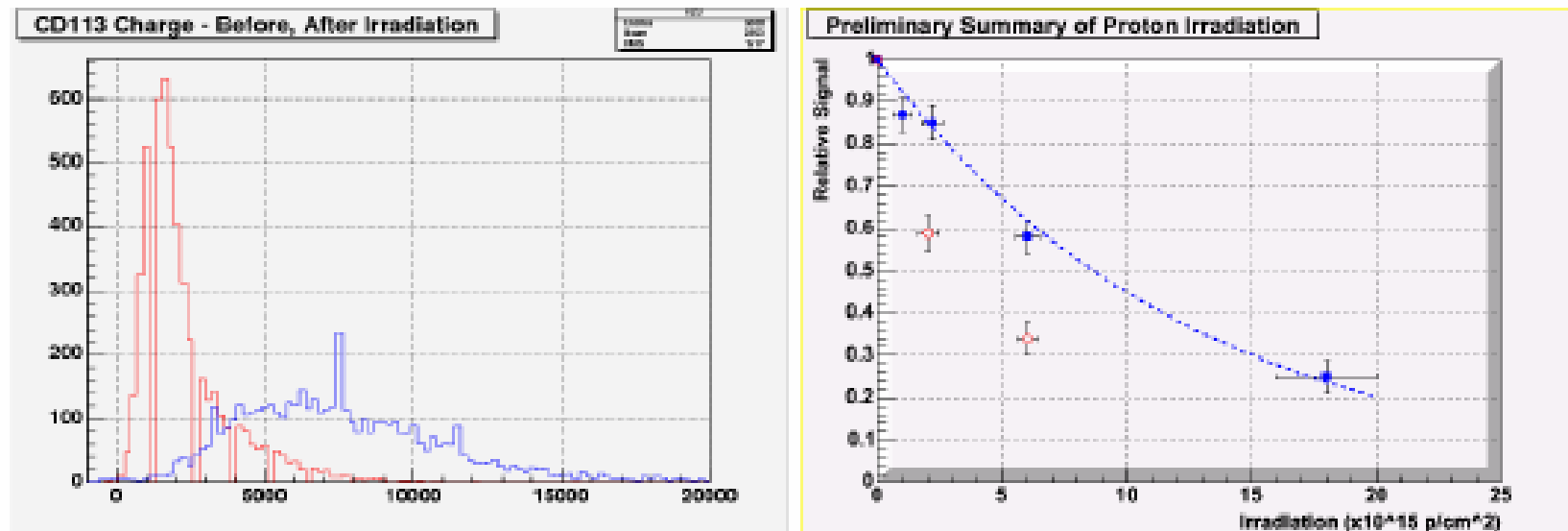
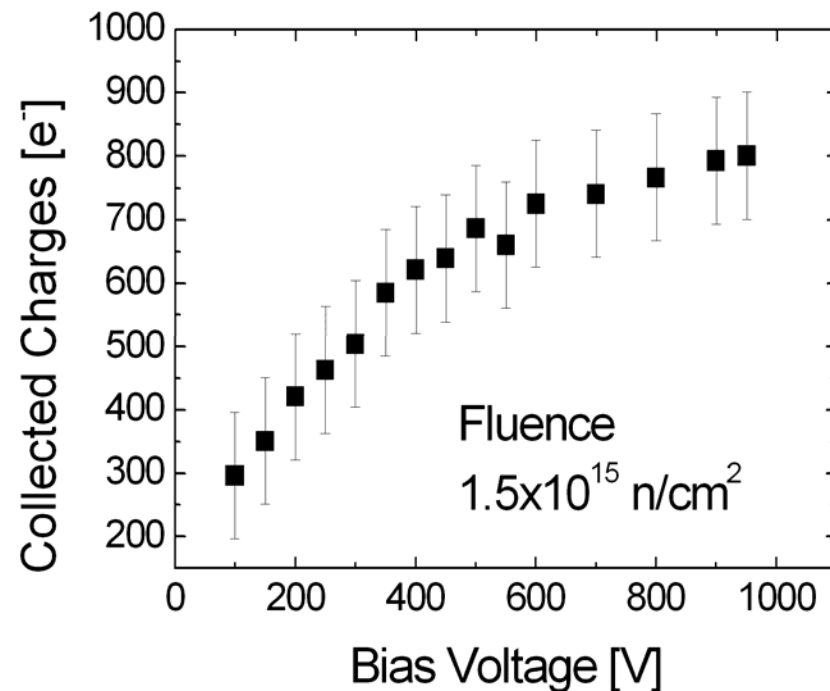
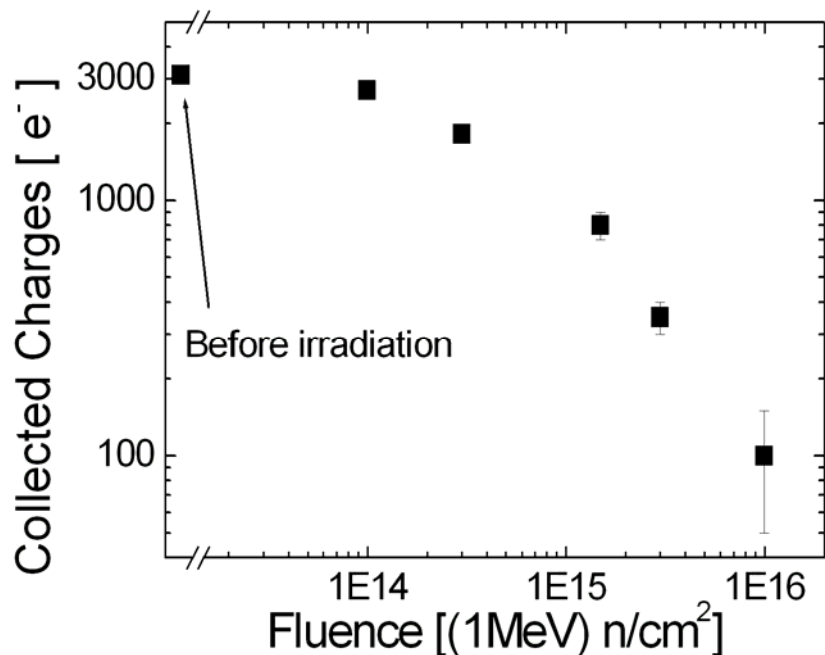


Figure 17: (a) Pulse height distributions before (blue curve) and after (red curve) the irradiation to $18 \times 10^{15} \text{ p/cm}^2$. (b) Summary of proton irradiation results for pCVD material up to a fluence of $20 \times 10^{15} \text{ p/cm}^2$ (filled data points). The blue curve is an exponential with exponent $-0.08 \times \text{fluence}$. Also shown are the results of the irradiation of the first scCVD diamond (open data points).

SiC (Data from Moscatelli et al. Rd50 7° Workshop Nov. 2005)

Epi-SiC: CCE 26% ($800 e^-$) after $1.5 \times 10^{15} \text{ n/cm}^2$ with epilayer of $50 \mu\text{m}$.



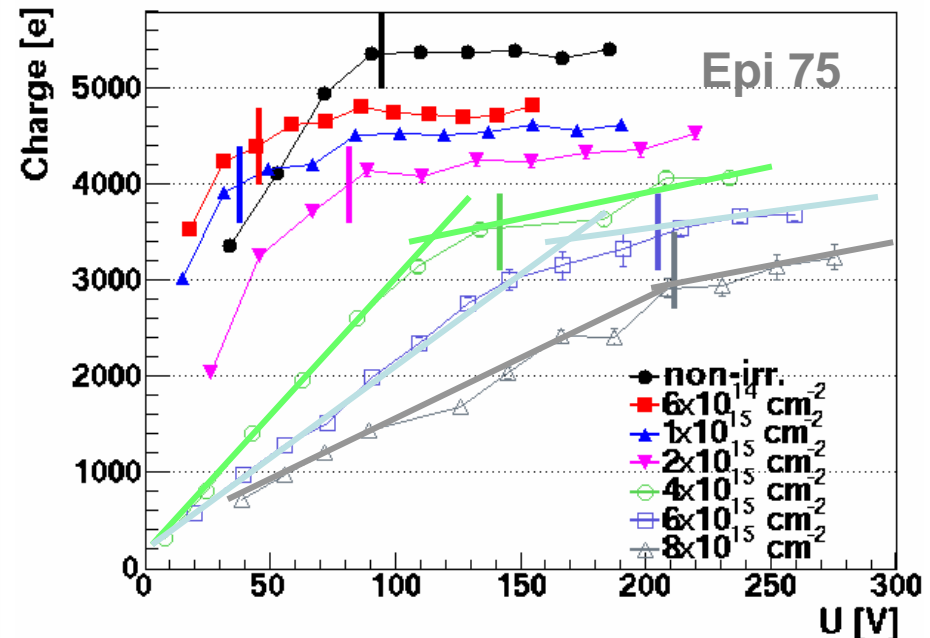
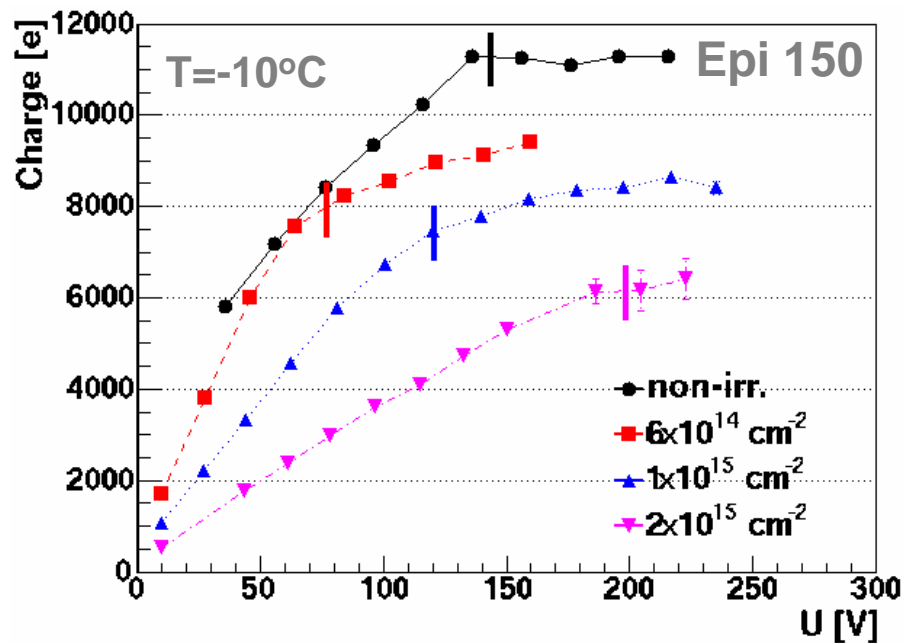
And from RESMDD05: $300 e^-$ at 600 V after $7 \times 10^{15} \text{ n/cm}^2$

S. Sciortino et al. "Effects of heavy proton and neutron irradiations on epitaxial SiC Schottky diodes", NIM A 552 (2005) 138-145.

Epitaxial Silicon Thick epilayers (75-150 μm)

M.I.P. measurements

V_{fd} from CV is denoted by short line for every sensor!



75 μm diodes perform superbly in term of noise (no break downs) also at very high fluences!

- kink in charge collection plot coincides with full depletion voltage from CV measurements! Also for heavily irradiated silicon detectors the full depletion voltage has meaning
- the signal for heavily irradiated sensors rises significantly after V_{fd} (trapping)
- >3200 e for $8 \times 10^{15} \text{ cm}^{-2}$ neutron irradiated sensor! – more than expected